

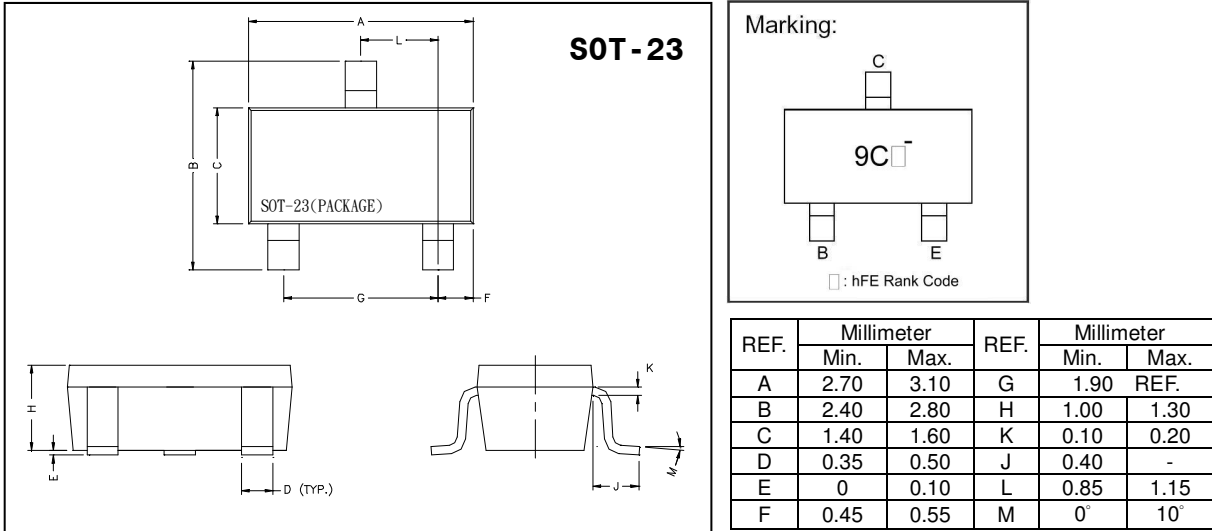
GBC858

PNP EPITAXIAL PLANAR TRANSISTOR

Description

The GBC858 is designed for switching and AF amplifier application, suitable for automatic insertion in thick and thin-film circuits.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Collector to Base Voltage	V _{CB0}	-30	V
Collector to Emitter Voltage	V _{CEO}	-30	V
Emitter to Base Voltage	V _{EBO}	-5	V
Collector Current	I _C	-100	mA
Total Power Dissipation	P _D	225	mW

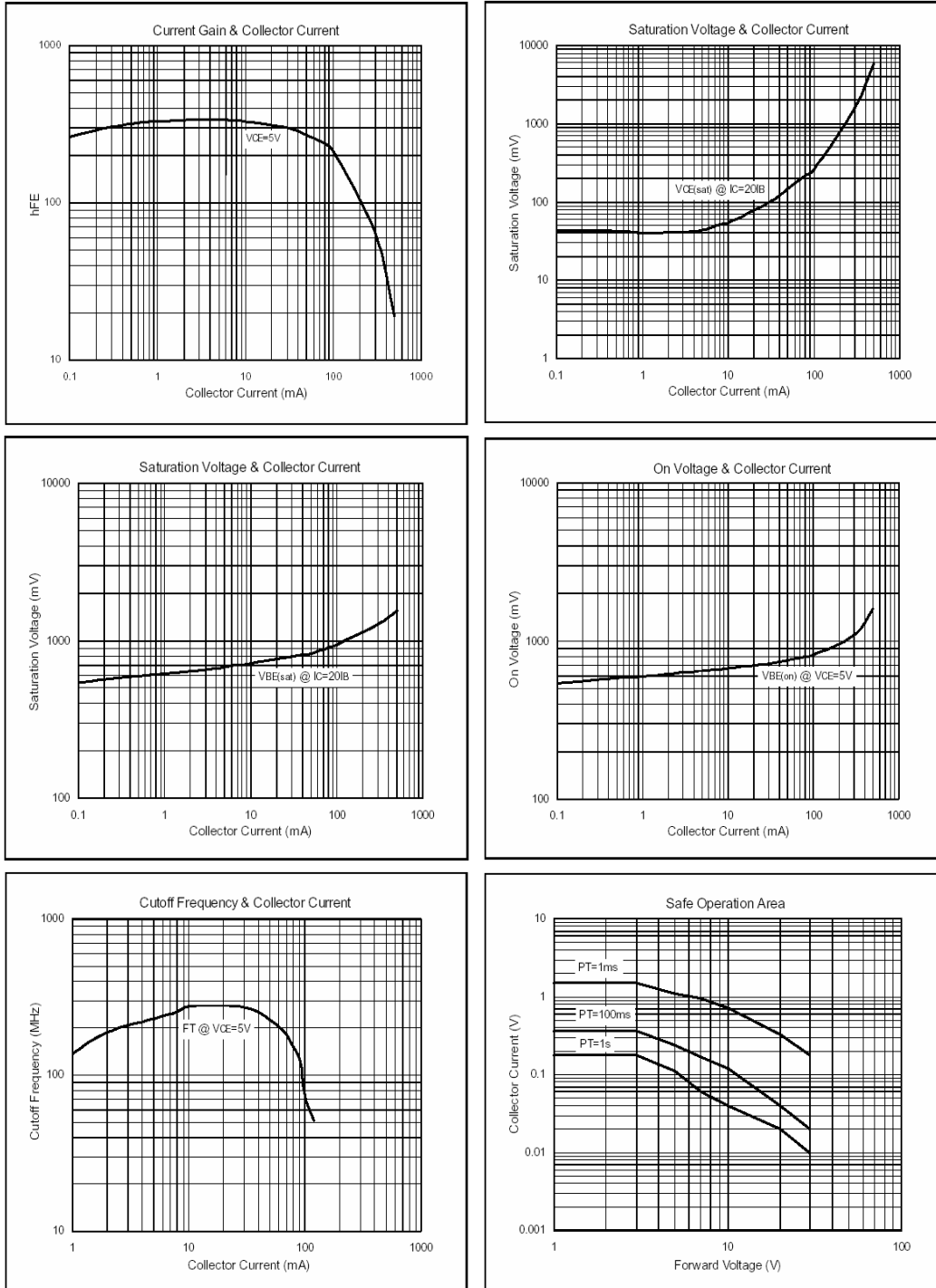
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V _{CB0}	-30	-	-	V	I _C =-100uA
V _{CEO}	-30	-	-	V	I _C =-1mA
V _{EBO}	-5	-	-	V	I _E =-10uA
I _{CB0}	-	-	-15	nA	V _{CB} =-30V
V _{CE(sat)1}	-	-90	-300	mV	I _C =-10mA, I _B =-0.5mA
V _{CE(sat)2}	-	-250	-650	mV	I _C =-100mA, I _B =-5mA
V _{BE(sat)1}	-	-700	-	mV	I _C =-10mA, I _B =-0.5mA
V _{BE(sat)2}	-	-900	-	mV	I _C =-100mA, I _B =-5mA
V _{BE(on)1}	-600	-	-750	mV	V _{CE} =-5V, I _C =-2mA
V _{BE(on)2}	-	-	-800	mV	V _{CE} =-5V, I _C =-10mA
h _{FE}	110	-	800		V _{CE} =-5V, I _C =-2mA
f _T	-	150	-	MHz	V _{CE} =-5V, I _C =-10mA
C _{ob}	-	-	6	pF	V _{CB} =-10V, f=1MHz, I _E =0A

Classification Of hFE

Rank	A	B	C
hFE	110-220	200-450	420-800

Characteristics Curve



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